Dual 2-input NAND gate Rev. 5 — 26 September 2013

1. General description

The 74HC2G00; 74HCT2G00 is a dual 2-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - ◆ For 74HC2G00: CMOS level
 - For 74HCT2G00: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package	ackage							
	Temperature range	Name	Description	Version					
74HC2G00DP	–40 °C to +125 °C	TSSOP8							
74HCT2G00DP			body width 3 mm; lead length 0.5 mm						
74HC2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads;	SOT765-1					
74HCT2G00DC			body width 2.3 mm						
74HC2G00GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads;	SOT996-2					
74HCT2G00GD			8 terminals; body $3 \times 2 \times 0.5$ mm						



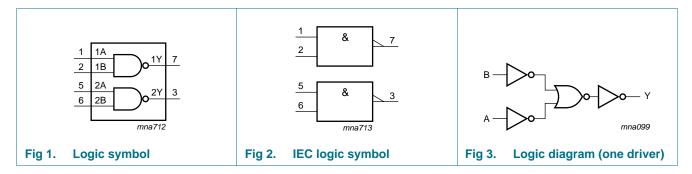
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4. Marking

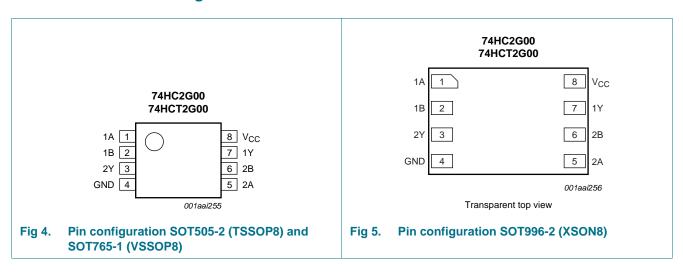
Table 2. Marking code	
Type number	Marking code ^[1]
74HC2G00DP	H00
74HCT2G00DP	Т00
74HC2G00DC	H00
74HCT2G00DC	Т00
74HC2G00GD	H00
74HCT2G00GD	Т00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information



6.1 Pinning

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6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4.Function table^[1]

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V_{l} < -0.5 V or V_{l} > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	V_O < –0.5 V or V_O > V_{CC} + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)	<u>[1]</u> -	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I _{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
PD	dynamic power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions		74HC2G00			74HCT2G00		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7.Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	–40 °C 1	-40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
74HC2G0	0								
V _{IH}	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V	
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V	
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V	
V _{IL}	LOW-level input voltage	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V	
		$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V	
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V	
V _{он}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V	
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V	
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V	
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V	
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V	
		$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V	
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V	
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V	
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V	
I	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	-	±1.0	μA	
сс	supply current	per input pin; $V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μΑ	
Ci	input capacitance		-	1.5	-	-	-	pF	

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Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
74HCT2G	00								
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V	
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V	
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V	
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V	
V _{OL}	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$							
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V	
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V	
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±1.0	-	±1.0	μA	
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	10	-	20	μA	
∆l _{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} - 2.1 V; I _O = 0 A	-	-	375	-	410	μA	
Cı	input capacitance		-	1.5	-	-	-	pF	

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25 \text{ }^{\circ}\text{C}$; for test circuit see Figure 7.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	–40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	-
74HC2G	00								
t _{pd}	propagation delay	nA and nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	25	95	-	110	ns
		$V_{CC} = 4.5 V$		-	9	19	-	22	ns
		$V_{CC} = 6.0 V$		-	7	16	-	20	ns
t _t	transition time	see <u>Figure 6</u>	[2]						
		$V_{CC} = 2.0 V$		-	18	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	19	-	25	ns
		$V_{CC} = 6.0 V$		-	5	16	-	20	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	<u>[3]</u>	-	10	-	-	-	pF

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Voltages	are referenced to G	ND (ground = 0 V); all typical valu	es are	measure	d at T _{amb}	=25 °C;	for test ci	rcuit see <mark>Fi</mark>	<u>gure 7</u> .
Symbol Parameter Cond		Conditions		–40 °C to +85 °C			–40 °C t	Unit	
				Min	Тур	Max	Min	Max	
74HCT2	G00								
t _{pd}	propagation delay	nA and nB to nY; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	12	24	-	29	ns
tt	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 6}}{1000}$	[2]	-	6	19	-	22	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5$ V	<u>[3]</u>	-	10	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

- [2] t_t is the same as t_{TLH} and t_{THL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_{I} = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms

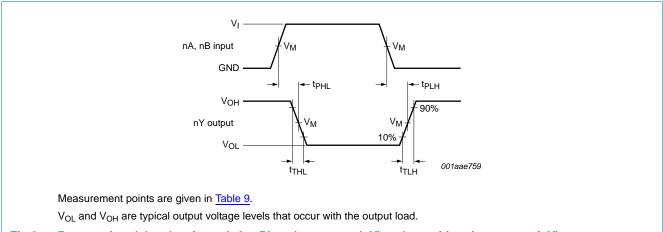


Fig 6. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)

Table 9. **Measurement points**

Туре	Input	Output
	V _M	V _M
74HC2G00	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G00	1.3 V	1.3 V

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74HC2G00; 74HCT2G00

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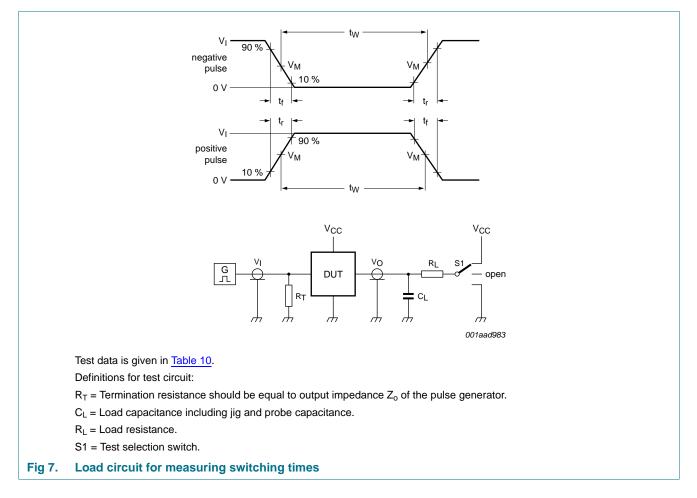


Table 10. Test data

Туре	Input		Load		S1 position
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74HC2G00	V _{CC}	≤ 6 ns	50 pF	1 kΩ	open
74HCT2G00	3 V	≤ 6 ns	50 pF	1 kΩ	open

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13. Package outline

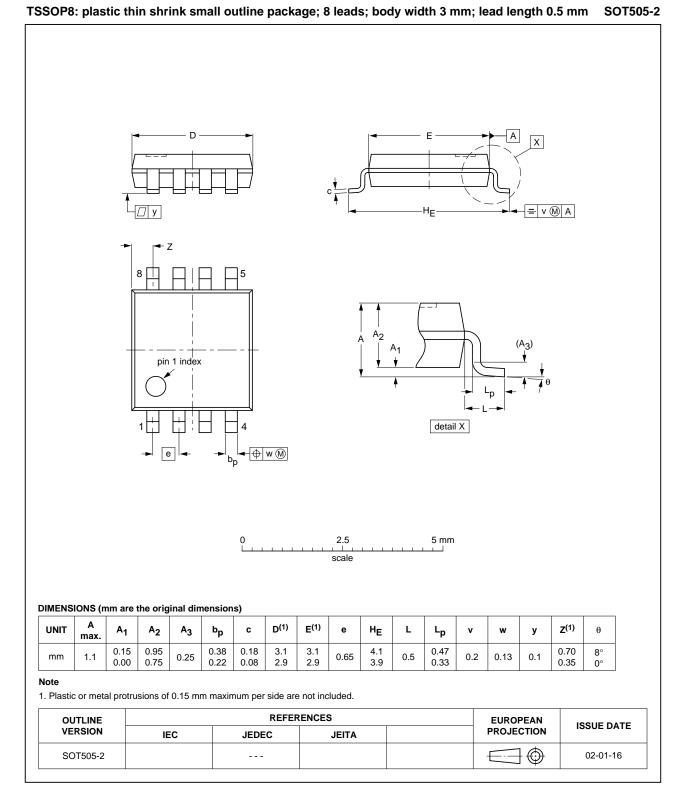


Fig 8. Package outline SOT505-2 (TSSOP8)

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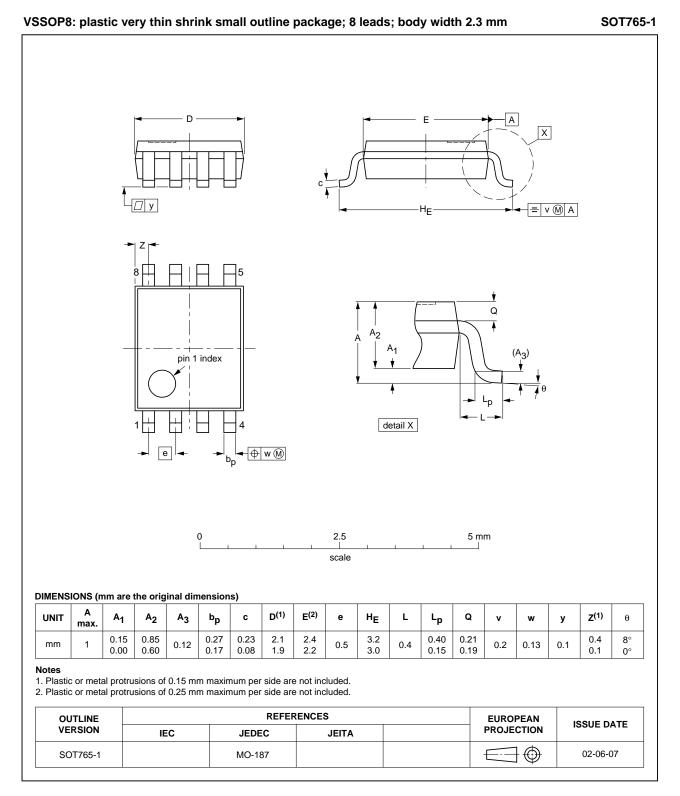
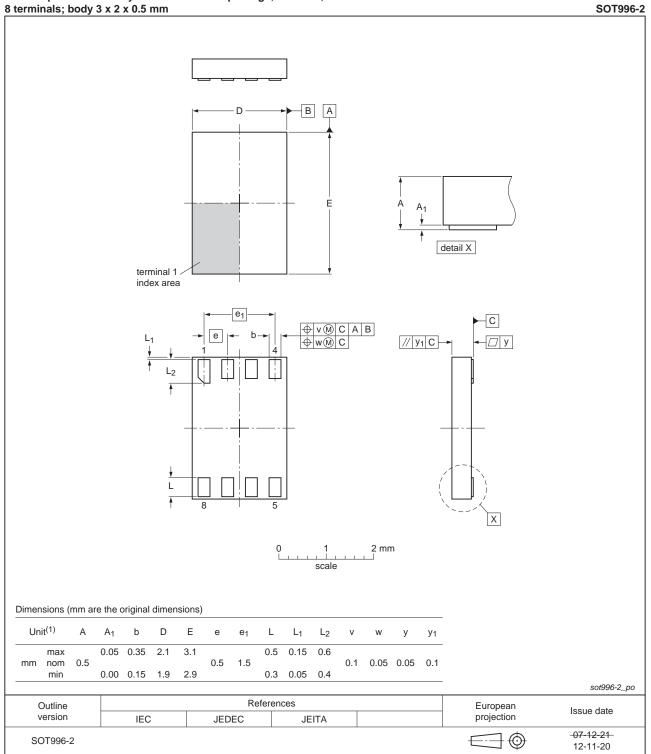


Fig 9. Package outline SOT765-1 (VSSOP8)

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XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

Fig 10. Package outline SOT996-2 (XSON8)

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14. Abbreviations

Table 11. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal-Oxide Semiconductor			
ESD	ElectroStatic Discharge			
НВМ	Human Body Model			
MM	Machine Model			
TTL	Transistor-Transistor Logic			

15. Revision history

Table 12. Revision history **Document ID Release date** Data sheet status Change notice Supersedes 74HC_HCT2G00 v.5 20130926 Product data sheet 74HC_HCT2G00 v.4 Modifications: • For type numbers 74HC2G00GD and 74HCT2G00GD XSON8U has changed to XSON8. 74HC_HCT2G00 v.4 20080703 Product data sheet 74HC_HCT2G00 v.3 _ 74HC_HCT2G00 v.3 Product data sheet 20060405 _ 74HC_HCT2G00 v.2 74HC_HCT2G00 v.2 20030212 Product specification 74HC_HCT2G00 v.1 -74HC_HCT2G00 v.1 20020710 Product specification --

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